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(54) **HIGH-THROUGHPUT HDP-CVD PROCESSES FOR ADVANCED GAPFILL APPLICATIONS**

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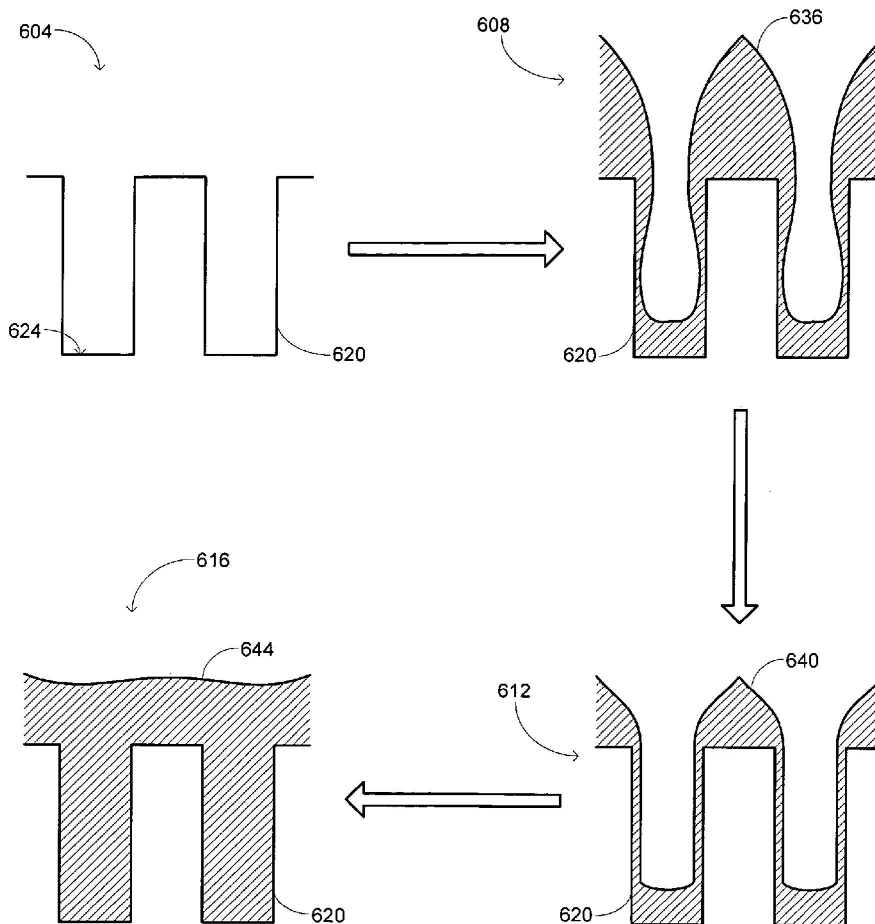
(57) **ABSTRACT**

Methods are provided of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber. The substrate has a gap formed between adjacent raised surfaces. A silicon-containing gas, an oxygen-containing gas, and a fluent gas are flowed into the substrate processing chamber. The fluent gas has an average molecular weight less than 5 amu. A first high-density plasma is formed from the silicon-containing gas, the oxygen-containing gas, and the fluent gas to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a first deposition/sputter ratio. A second high-density plasma is formed from the silicon-containing gas, the oxygen-containing gas, and the fluent gas to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a second deposition/sputter ratio. The second deposition/sputter ratio is less than the first deposition/sputter ratio. Each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.



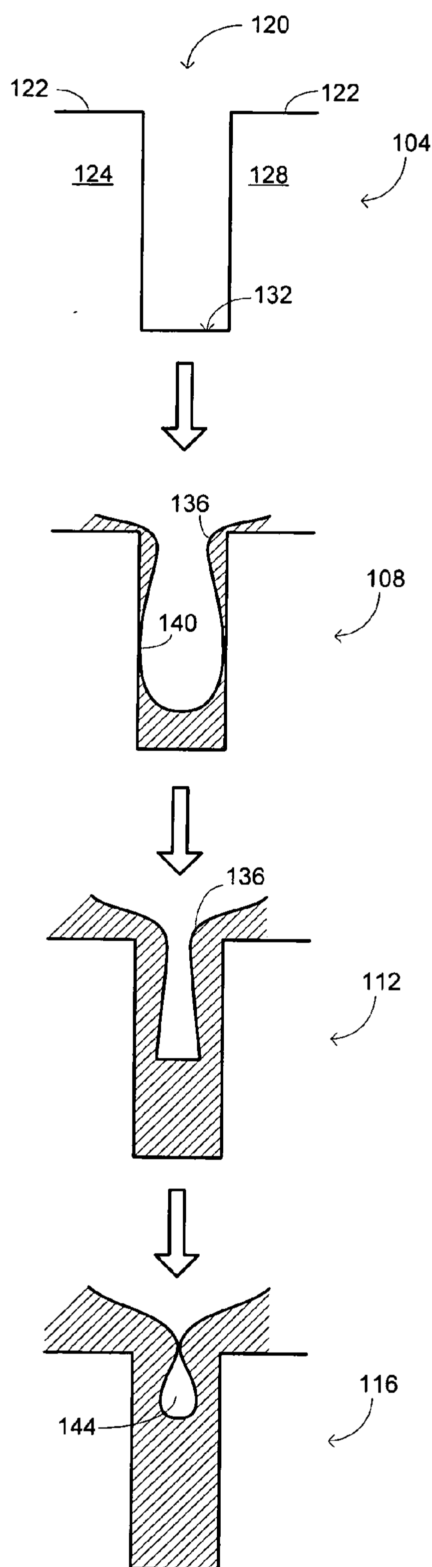


Fig. 1
(Prior Art)

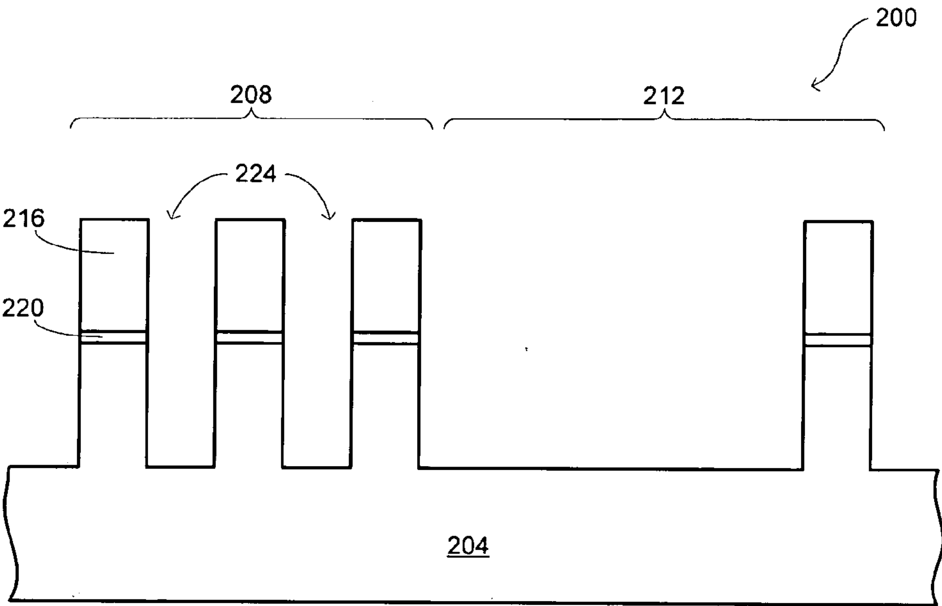


Fig. 2

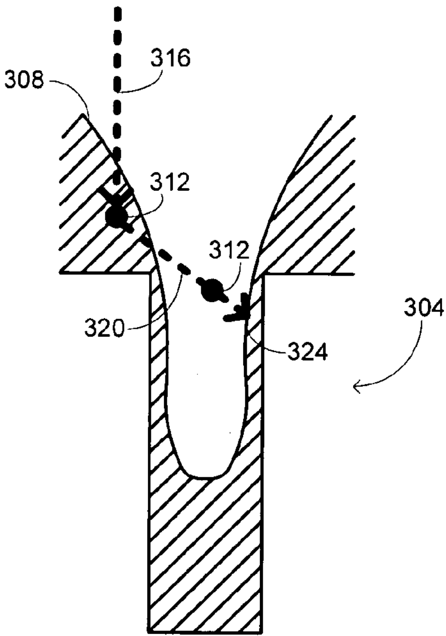


Fig. 3A

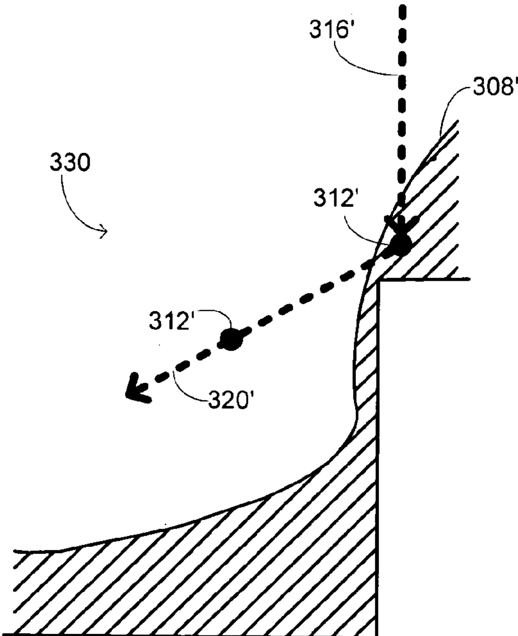


Fig. 3B

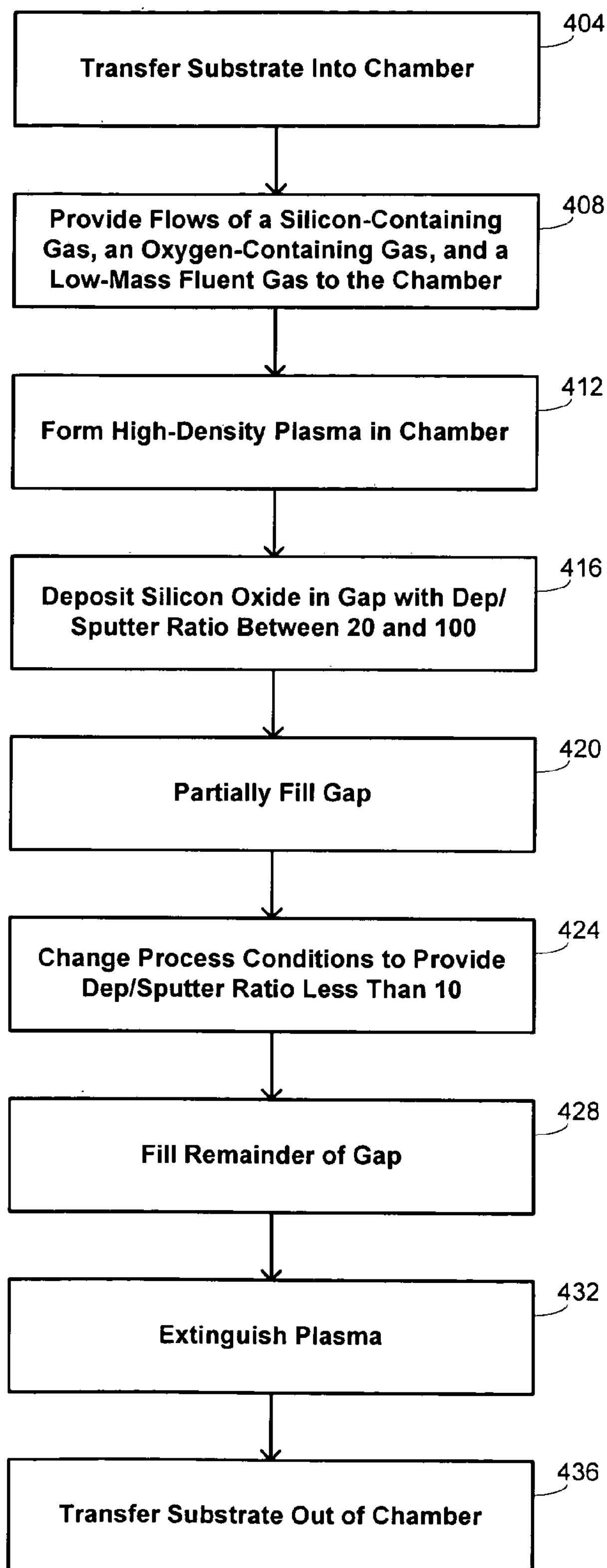


Fig. 4

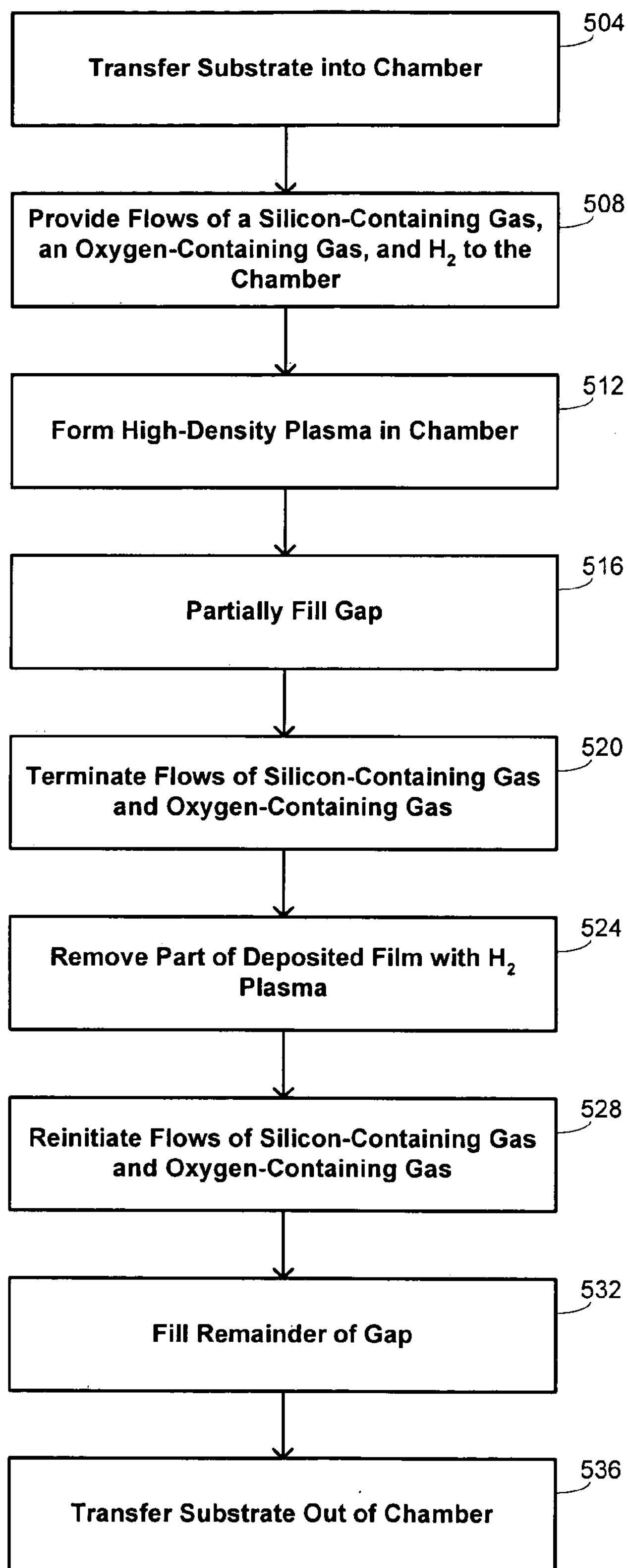


Fig. 5

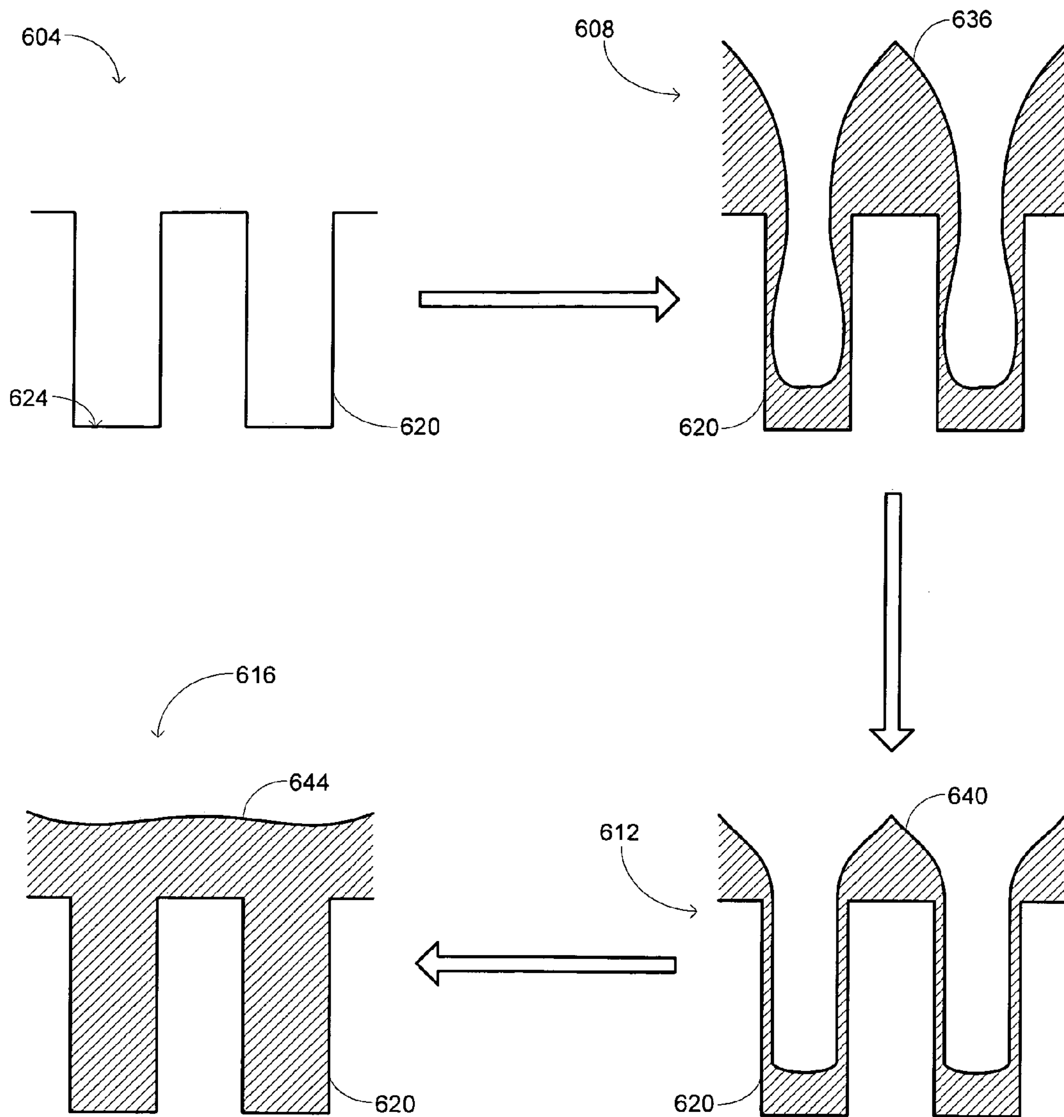


Fig. 6

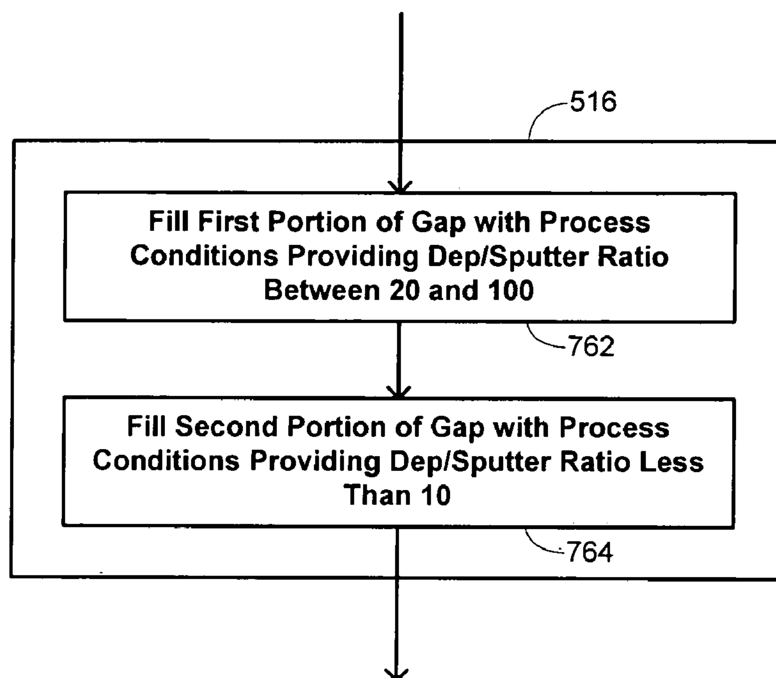


Fig. 7A

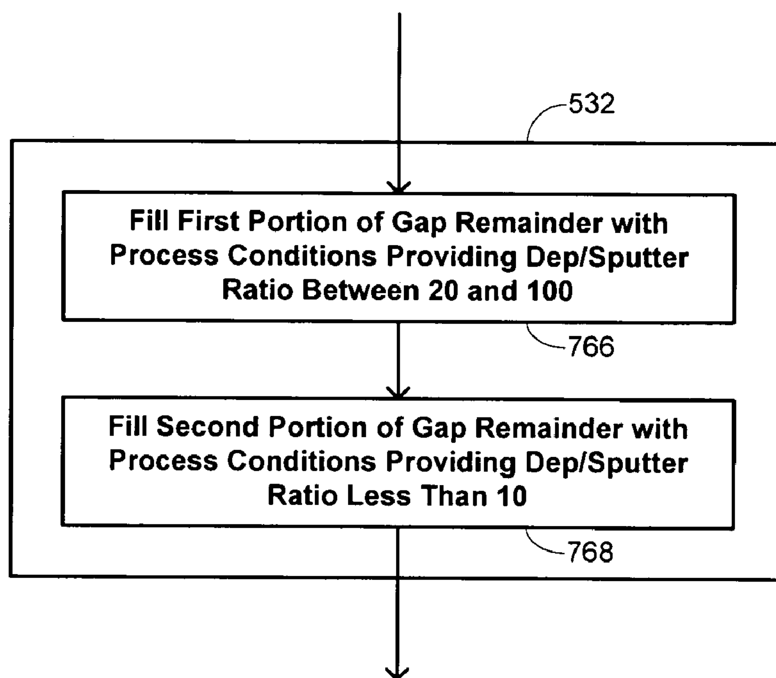


Fig. 7B

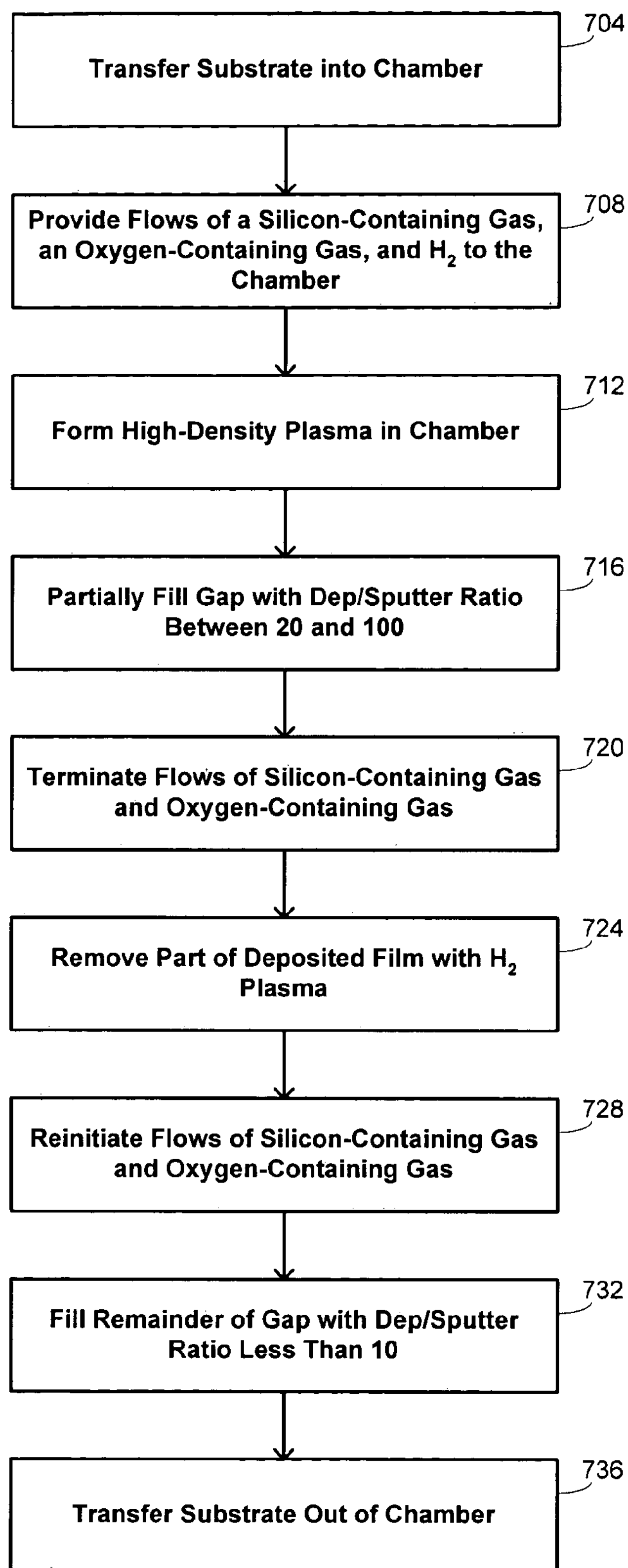
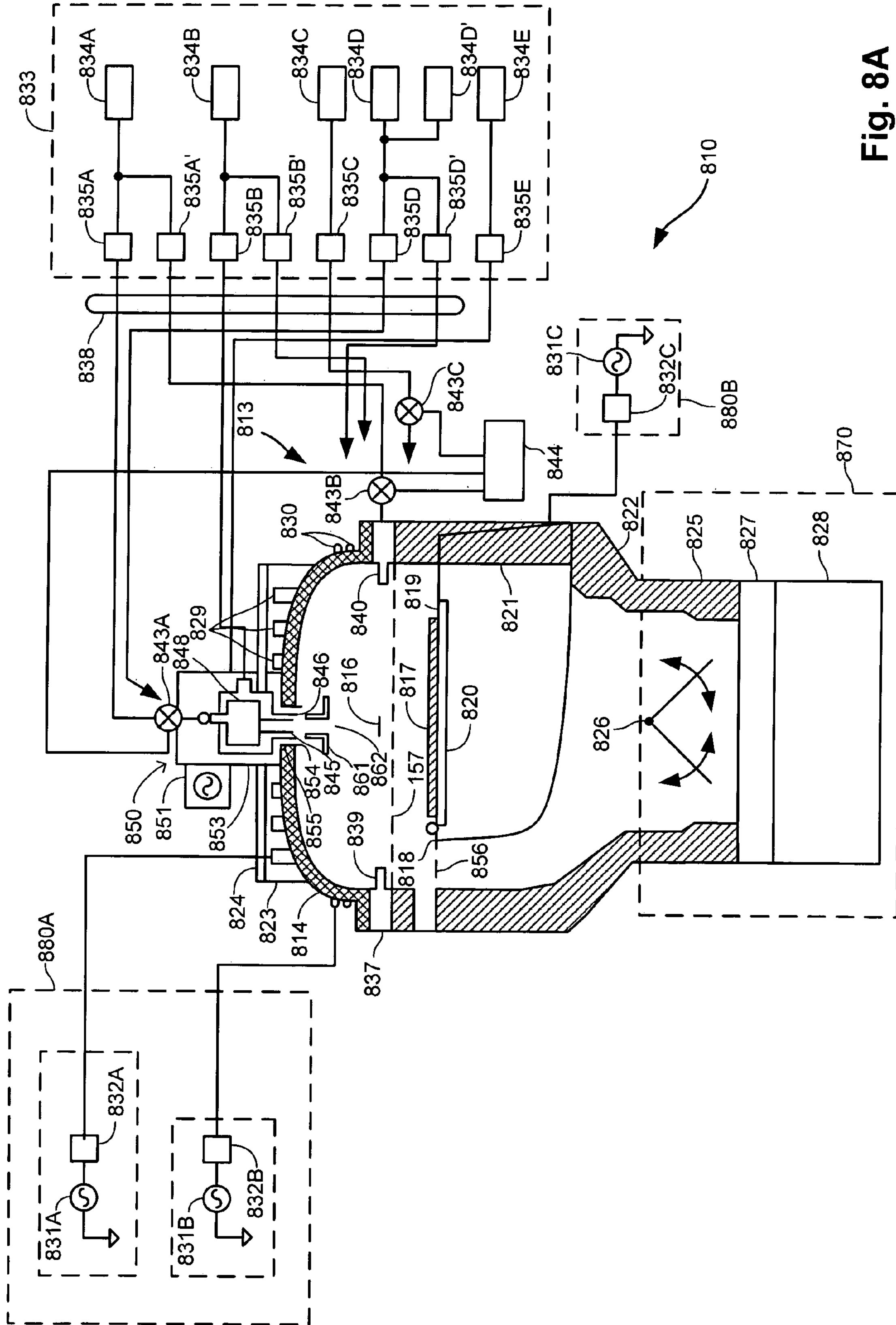


Fig. 7C


833
834A
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831C
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843C
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Fig. 8A

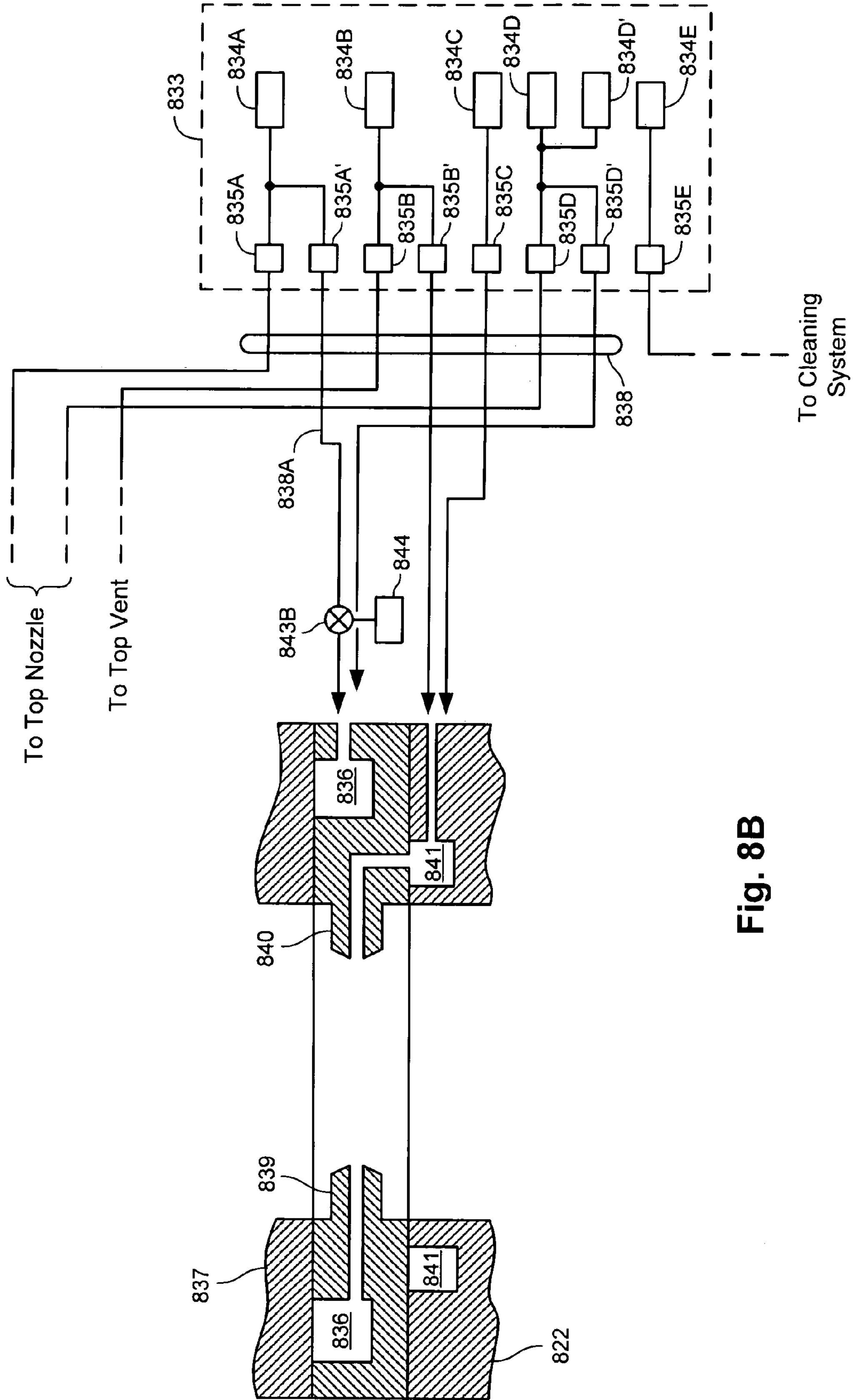

Fig. 8B

HIGH-THROUGHPUT HDP-CVD PROCESSES FOR ADVANCED GAPFILL APPLICATIONS

BACKGROUND OF THE INVENTION

[0001] One of the persistent challenges faced in the development of semiconductor technology is the desire to increase the density of circuit elements and interconnections on substrates without introducing spurious interactions between them. Unwanted interactions are typically prevented by providing gaps or trenches that are filled with electrically insulative material to isolate the elements both physically and electrically. As circuit densities increase, however, the widths of these gaps decrease, increasing their aspect ratios and making it progressively more difficult to fill the gaps without leaving voids. The formation of voids when the gap is not filled completely is undesirable because they may adversely affect operation of the completed device, such as by trapping impurities within the insulative material.

[0002] Common techniques that are used in such gapfill applications are chemical-vapor deposition ("CVD") techniques. Conventional thermal CVD processes supply reactive gases to the substrate surface where heat-induced chemical reactions take place to produce a desired film. Plasma-enhanced CVD ("PECVD") techniques promote excitation and/or dissociation of the reactant gases by the application of radio-frequency ("RF") energy to a reaction zone near the substrate surface, thereby creating a plasma. The high reactivity of the species in the plasma reduces the energy required for a chemical reaction to take place, and thus lowers the temperature required for such CVD processes when compared with conventional thermal CVD processes. These advantages may be further exploited by high-density-plasma ("HDP") CVD techniques, in which a dense plasma is formed at low vacuum pressures so that the plasma species are even more reactive. While each of these techniques falls broadly under the umbrella of "CVD techniques," each of them has characteristic properties that make them more or less suitable for certain specific applications.

[0003] HDP-CVD systems form a plasma that is at least approximately two orders of magnitude greater than the density of a standard, capacitively coupled plasma CVD system. Examples of HDP-CVD systems include inductively coupled plasma systems and electron cyclotron resonance (ECR) plasma systems, among others. HDP-CVD systems generally operate at lower pressure ranges than low-density plasma systems. The low chamber pressure employed in HDP-CVD systems provides active species having a long mean-free-path and reduced angular distribution. These factors, in combination with the plasma density, contribute to a significant number of constituents from the plasma reaching even the deepest portions of closely spaced gaps, providing a film with improved gapfill capabilities compared with films deposited in a low-density plasma CVD system.

[0004] Another factor that allows films deposited by HDP-CVD techniques to have improved gapfill characteristics is the promotion of sputtering by the high density of the plasma, simultaneous with film deposition. The sputtering component of HDP deposition processes slows deposition on certain features, such as the corners of raised surfaces, thereby contributing to the increased gapfill ability of HDP deposited films. Some HDP-CVD systems introduce argon or a similar heavy inert gas to further promote the sputtering effect. These HDP-CVD systems typically employ an electrode within the substrate support pedestal that enables the creation of an electric field to bias the plasma towards the substrate. The electric field can be applied throughout the HDP deposition process for further promotion of sputtering and to provide better gapfill characteristics for a given film.

[0005] It was initially thought that because of their simultaneous deposition/sputter nature, HDP-CVD processes could fill the gaps or trenches that were created in almost any application. Semiconductor manufacturers have discovered, however, that there is a practical limit to the aspect ratio of gaps that HDP-CVD processes are able to fill. For example, one HDP-CVD process commonly used to deposit a silicon oxide gapfill film forms a plasma from a process gas that includes silane SiH_4, molecular oxygen O_2, and argon Ar. It has been reported that when such a process is used to fill certain narrow-width high-aspect-ratio gaps, the sputtering caused by argon in the process gas may hamper the gapfill efforts. Specifically, it has been reported that material sputtered by argon in the process redeposits on the upper portions of the sidewalls of the gaps being filled at a rate faster than at the lower portions. This, in turn, may result in the formation of a void in the gap if the upper areas of regrowth join before the gap is completely filled.

[0006] **FIG. 1** provides schematic cross-sectional views of a silicon oxide film at different stages of deposition to illustrate the potential gapfill limitation associated with some CVD processes. The gapfill problem is illustrated in somewhat exaggerated form to illustrate the problem better. The top portion of **FIG. 1** shows the initial structure **104** in which a gap **120** is defined by two adjacent features **124** and **128** having horizontal surfaces **122**, with the horizontal surface at the bottom of the gap being denoted **132**. As shown in structure **108**, i.e. the second portion of the figure from the top, a conventional HDP-CVD silicon oxide deposition process results in direct deposition on the horizontal surface **132** at the bottom of the gap **120** and on the horizontal surfaces **122** above the features **124** and **128**. It also, however, results in indirect deposition (referred to as "redeposition") on the sidewalls **140** of the gap **120** due to recombination of material sputtered from the silicon oxide film as it grows. In certain small-width, high-aspect-ratio applications, the continued growth of the silicon oxide film results in formations **136** on the upper section of the sidewall **140** that grow towards each other at a rate of growth exceeding the rate at which the film grows laterally on the lower portions of the sidewall. This trend is shown in structures **108** and **112**, with the final result in structure **116** being the formation of a void **144** within the film. The probability of forming a void is very directly related to the rate and character of the redeposition.

[0007] There accordingly remains a general need in the art for improving gapfill techniques.

BRIEF SUMMARY OF THE INVENTION

[0008] Embodiments of the invention provide methods of depositing a silicon oxide film that improve gapfill capabilities. Some embodiments that are especially suitable for substrates that have both dense and open areas and fill part of the gaps with an initially higher deposition contribution from an HDP-CVD process, followed by a lower deposition

contribution to fill a further portion of the gaps. Other embodiments make use of an unexpected chemical effect with a hydrogen-based plasma to remove material intermediate between deposition phases to reopen the gap before formation of a void. In some instances, these embodiments overlap with certain processes making use of both aspects.

[0009] Thus, in a first set of embodiments, a method is provided of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber. The substrate has a gap formed between adjacent raised surfaces. A silicon-containing gas, an oxygen-containing gas, and a fluent gas are flowed into the substrate processing chamber. The fluent gas has an average molecular weight less than 5 amu. A first high-density plasma is formed from the silicon-containing gas, the oxygen-containing gas, and the fluent gas to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a first deposition/sputter ratio. A second high-density plasma is formed from the silicon-containing gas, the oxygen-containing gas, and the fluent gas to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a second deposition/sputter ratio. The second deposition/sputter ratio is less than the first deposition/sputter ratio. Each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

[0010] In some embodiments, the first deposition/sputter ratio is between 20 and 100. Also in some embodiments, the second deposition/sputter ratio is less than 10. The second high-density plasma may be formed by changing process conditions without extinguishing the first high-density plasma. The fluent gas may comprise molecular hydrogen H_2 and may be flowed into the substrate processing chamber with a flow rate greater than 500 sccm. In another embodiment, the fluent gas comprises helium He. The silicon-containing gas may comprise monosilane SiH_4 and the oxygen-containing gas may comprise molecular oxygen O_2. In one embodiment, the first portion of the silicon oxide film reduces a depth of the gap by less than 50%. In some instances, the gap may comprise a plurality of gaps formed between adjacent raised surfaces, with a first of the gaps having a width at least five times a width of a second of the gaps.

[0011] In a second set of embodiments, a method is also provided for depositing a silicon oxide film on a substrate disposed in a substrate processing chamber. The substrate has a gap formed between adjacent raised surfaces. A flow of a first gaseous mixture is provided to the substrate processing chamber. The first gaseous mixture comprises a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas. A first high-density plasma is formed from the first gaseous mixture to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components. The first portion of the silicon oxide film is exposed to a second high-density plasma formed with a flow of gases having an average molecular weight less than 5 amu and including a flow of molecular hydrogen H_2. Thereafter, a flow of a second gaseous mixture is provided to the substrate processing chamber. The flow of the second gaseous mixture comprises a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas. A third high-density plasma is formed from the second gaseous mixture to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components.

[0012] In some such embodiments, the second high-density plasma is formed with a flow that consists essentially of molecular hydrogen H_2. The first portion may be exposed to the second high-density plasma by terminating the flow of the silicon-containing gas and the flow of the oxygen-containing gas comprised by the flow of the first gaseous mixture. In addition, the flow of the second gaseous mixture may be provided by reinitiating the terminated flow of the silicon-containing gas and the terminated flow of the oxygen-containing gas. The flow rate of molecular hydrogen H_2 may be provided at a rate greater than 500 sccm in some embodiments, and may be provided at a rate greater than 1000 sccm in other embodiments.

[0013] The process may be cycled repeatedly. For example, in one embodiment, the second portion of the silicon oxide film is exposed to a fourth high-density plasma formed with a flow of gases having an average molecular weight less than 5 amu and including a flow of molecular hydrogen. Thereafter, a flow of a third gaseous mixture is provided to the substrate processing chamber. The flow of the third gaseous mixture comprises a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas. A fifth high-density plasma is formed from the third gaseous mixture to deposit a third portion of the silicon oxide film over the substrate and within the gap with a third deposition process that has simultaneous deposition and sputtering components.

[0014] In addition, relative deposition and sputtering contributions may be varied during different depositions. For example the first deposition process may comprise relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100, and the second deposition process may comprise deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10. In other instance, the first deposition process may comprise a first part having relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100, followed by a second part having relative deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10. Similarly, the second deposition process may comprise a first part having relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100, followed by a second part having relative deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10.

[0015] A further understanding of the nature and advantages of the present invention may be realized by reference to the remaining portions of the specification and the drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0016] **FIG. 1** provides schematic cross-sectional drawings illustrating the formation of a void during a prior-art gapfill process;

[0017] **FIG. 2** is a simplified cross-sectional view of a partially completed integrated circuit that includes a plurality of shallow-trench-isolation structures;

[0018] **FIGS. 3A and 3B** are schematic diagrams that respectively illustrated gapfill characteristics of densely packed areas and open areas in a structure;

[0019] **FIG. 4** is a flow diagram illustrating a method for depositing a film in one embodiment of the invention;

[0020] **FIG. 5** is a flow diagram illustrating a method for depositing a film in another embodiment of the invention;

[0021] **FIG. 6** provides schematic diagrams illustrating how material is deposited in a gap using the method of **FIG. 5**;

[0022] **FIGS. 7A-7C** are flow diagrams that illustrate alternative methods for depositing a film in other embodiments of the invention;

[0023] **FIG. 8A** is a simplified diagram of one embodiment of a high-density-plasma chemical-vapor-deposition system with which methods of the invention may be implemented; and

[0024] **FIG. 8B** is a simplified cross section of a gas ring that may be used in conjunction with the exemplary processing system of **FIG. 8A**.

DETAILED DESCRIPTION OF THE INVENTION

[0025] Embodiments of the invention are directed to methods of depositing a silicon oxide layer to fill a gap in a surface of a substrate using a high-density-plasma CVD process. Silicon oxide films deposited according to the techniques of the invention have excellent gapfill capabilities and are able to fill gaps encountered in, for example, shallow-trench-isolation ("STI") structures. Films deposited by the methods of the invention are thus suitable for use in the fabrication of a variety of integrated circuits.

[0026] The types of structures that may be filled according to embodiments of the invention are illustrated by **FIG. 2**, which provides a simplified cross-sectional view of a partially completed integrated circuit **200**. This integrated circuit is formed over a substrate **204** that includes a plurality of STI structures, each of which is typically created by forming a thin pad oxide layer **220** over the surface of the substrate **204** and then forming a silicon nitride layer **216** over the pad oxide layer **220**. The nitride and oxide layers are then patterned using standard photolithography techniques and trenches **224** are etched through the nitride/oxide stack into the substrate **204**. **FIG. 2** shows that the integrated circuit may comprise areas **208** that are relatively densely packed with transistors or other active devices, and may comprise open areas **212** that are relatively isolated. Active devices in the open areas **212** may be separated from each other by more than an order of magnitude than separations in the densely packed areas **208**, but as used herein "open areas" are considered to be areas in which gaps have a width at least five times a width of a gap in a "dense area."

[0027] Embodiments of the invention provide methods for filling the trenches **224** with an electrically insulating material such as silicon dioxide using a deposition process that has good gapfill properties. Different embodiments of the invention are more suitable for filling gaps in the open areas, while other embodiments of the invention are especially suitable for filling the very high aspect-ratio gaps in the dense areas. In some instances, the gapfill characteristics provided by the methods described below have good gapfill capabilities in both the open and dense areas, making such techniques especially valuable for certain applications. In some instances, prior to the gapfill process, an initial lining layer is deposited over the substrate as an in situ steam generation ("ISSG") or other thermal oxide layer, or perhaps a silicon nitride layer. One benefit to depositing such a liner prior to filling the trenches **224** is to provide appropriate corner rounding, which may aid in avoiding such effects as early gate breakdown in transistors that are formed. In addition, such a liner may aid in relieving stress after the CVD deposition.

[0028] As used herein, a high-density-plasma process is a plasma CVD process that includes simultaneous deposition and sputtering components and that employs a plasma having an ion density on the order of 10^{11} ions/cm^3 or greater. The relative levels of the combined deposition and sputtering characteristics of the high-density plasma may depend on such factors as the flow rates used to provide the gaseous mixture, the source power levels applied to maintain the plasma, the bias power applied to the substrate, and the like. The combination of such factors may conveniently be quantified with a "deposition/sputter ratio," sometimes denoted D/S to characterize the process:

$$\frac{D}{S} \equiv \frac{(\text{net deposition rate}) + (\text{blanket sputtering rate})}{(\text{blanket sputtering rate})}.$$

The deposition/sputter ratio increases with increased deposition and decreases with increased sputtering. As used in the definition of D/S, the "net deposition rate" refers to the deposition rate that is measured when deposition and sputtering are occurring simultaneously. The "blanket sputter rate" is the sputter rate measured when the process recipe is run without deposition gases; the pressure within the process chamber is adjusted to the pressure during deposition and the sputter rate measured on a blanket thermal oxide.

[0029] Other equivalent measures may be used to quantify the relative deposition and sputtering contributions of the HDP process, as is known to those of skill in the art. A common alternative ratio is the "etching/deposition ratio,"

$$\frac{E}{D} \equiv \frac{(\text{source-only deposition rate}) - (\text{net deposition rate})}{(\text{source-deposition rate})},$$

which increases with increased sputtering and decreases with increased deposition. As used in the definition of E/D, the "net deposition rate" again refers to the deposition rate measured when deposition and sputtering are occurring simultaneously. The "source-only deposition rate," however, refers to the deposition rate that is measured when the

process recipe is run with no sputtering. Embodiments of the invention are described herein in terms of D/S ratios. While D/S and E/D are not precise reciprocals, they are inversely related and conversion between them will be understood to those of skill in the art.

[0030] The desired D/S ratios for a given step in the HDP-CVD processes are generally achieved by including flows of precursor gases and, in some instances, flows of a fluent gas, which may also act as a sputtering agent. The elements comprised by the precursor gases react to form the film with the desired composition. For example, to deposit a silicon oxide film, the precursor gases may include a silicon-containing gas, such as silane SiH_4, and an oxidizing gas reactant such as molecular oxygen O_2. Dopants may be added to the film by including a precursor gas with the desired dopant, such as by including a flow of SiF_4 to fluorinate the film, including a flow of PH_3 to phosphorate the film, including a flow of B_2H_6 to boronate the film, including a flow of N_2 to nitrogenate the film, and the like. The fluent gas may be provided with a flow of H_2 or with a flow of an inert gas, including a flow of He, or even a flow a heavier inert gas, such as Ne, Ar, or Xe. The level of sputtering provided by the different fluent gases is inversely related to their atomic mass (or molecular mass in the case of H_2), with H_2 producing even less sputtering than He. Embodiments of the invention generally provide fluent-gas flows that have an average molecular mass less than 5 amu. This may be achieved by using flows of a single low-mass gas, such as with a flow of substantially pure H_2 or with a flow of substantially pure He. Alternatively, flows may sometimes be provided of multiple gases, such as by providing both a flow of H_2 and a flow of He, which mix in the HDP-CVD process chamber. Alternatively, the gas may sometimes be premixed so that a flow of H_2/He is provided in a mixed state to the process chamber. It is also possible to provide separate flows of higher-mass gases, or to include higher-mass gases in the premixture, with the relative flow rates and/or concentrations of the premixture being selected to maintain an average molecular mass less than 5 amu.

[0031] In high-aspect-ratio structures, the use of relatively high flow rates of low-mass fluent gases has been found generally to improve gapfill capability when compared with the more traditional use of fluent gases such as Ar. This is believed to be a consequence of the reduction in redeposition that is achieved by using He or H_2 as a fluent gas so that closure of the gap occurs less quickly. The inventors have discovered, however, that the use of such a low-mass fluent gas results in increased corner clipping in open regions. This effect may be understood with reference to **FIGS. 3A and 3B**, which show the effect of the sputtering component of an HDP process respectively for a gap in a densely packed area and for a gap in an open area.

[0032] In particular, the gap **304** in **FIG. 3A** is a high-aspect-ratio gap, with the material deposited using an HDP-CVD process forming a characteristic cusp structure **308** over the horizontal surfaces. Redeposition occurs as material **312** is sputtered from the cusp **308** in response to the impact of plasma ions along path **316**. The sputtered material **312** follows a path **320** that encounters the sidewall **324** on the opposite side of the gap **304**. This effect is symmetrical so that as material is sputtered away from the left side of the gap onto the right side, material is also sputtered away from the right side of the gap onto the left side. The redeposition of material protects against excess sputtering resulting in clipping of the corners.

[0033] This symmetry is not present in the open areas, as illustrated with the open-area structure **330** shown in **FIG. 3B**. in this instance, the deposition causes the formation of a similar cusp **308'**, but when material **312'** is sputtered along path **320'** in response to the impact of plasma ions along path **316'**, the opposite side of the gap is too far away for the redeposition to be protective. The corner of the structure in **FIG. 3B** suffers the same ejection of material as does the corner of the structure in **FIG. 3A**, without the compensating effect of receiving material sputtered from the opposite side of the gap. As a consequence, there is an increased risk of clipping the corner and damaging the underlying structure.

[0034] In an embodiment of the invention, such corner clipping is avoided in open areas by using a process that has an initially high D/S ratio so that the initial part of the process is dominated by a greater deposition component and a reduced sputtering component. Subsequently, after some material has been deposited to protect the underlying structure, the D/S ratio is decreased so that the increased sputtering component keeps the gap open as material is deposited to complete gapfill. This decrease in D/S ratio during the process is used to address a combination of effects resulting from the use of a low-mass fluent gas in combination with a gap structure that does not benefit as strongly from redeposition effects. Such a decrease in D/S ratio is generally counter to more traditional gapfill techniques that increase the D/S ratio to improve gapfill with an initially aggressive gap.

[0035] An exemplary process that uses this technique is illustrated with the flow diagram of **FIG. 4**. The process begins at block **404** by transferring a substrate into a process chamber. The substrate is typically a semiconductor wafer, such as a 200-mm or 300-mm-diameter silicon wafer. Flows of precursor gases are provided to the chamber at block **408**, including a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a low-mass fluent gas. Table I provides exemplary flow rates for deposition of an undoped silicate glass ("USG") film using flows of monosilane SiH_4, molecular oxygen O_2, and H_2, although it should be understood that other precursor gases, including dopant sources, and other fluent gases that provide an average molecular mass less than 5 amu may be used as discussed above.

TABLE I

Exemplary Flow Rates for USG Deposition

Flow Rates for 200-mm Wafer Process		Flow Rates for 300-mm Wafer Process	
$F(SiH_4)$	10–60 sccm	$F(SiH_4)$	10–60 sccm
$F(O_2)$	20–120 sccm	$F(O_2)$	20–120 sccm
$F(H_2)$	400–1000 sccm	$F(H_2)$	750–1600 sccm

As the table indicates, the flow rates of the precursor gases may be similar for 200-mm and 300-mm-diameter wafers, but the flow rate of the fluent gas is generally higher.

[0036] A high-density plasma is formed from the gaseous flows at block **412** by coupling energy into the chamber. A

common technique for generating a high-density plasma is to couple rf energy inductively. The D/S ratio is determined not only by the flow rates for the gases, but also by the power density of energy coupled into the chamber, by the strength of a bias that may be applied to the substrate, by the temperature within the chamber, by the pressure within the chamber, and other such factors. For deposition of an initial portion of the film, such processing parameters are selected to provide a D/S ratio within the range of 20-100, as indicated at block **416**. Deposition is permitted to proceed with such a D/S ratio to fill the gap partially, as indicated at block **420**, with the process conditions being changed to provide a lower D/S ratio at block **424**. In some embodiments, the gap is filled at block **420** so that its depth is reduced by less than 50% from its initial depth. For instance, if the gap had an initial depth of 5.4 μm, as might occur for a gap having an aspect ratio of 6:1 and a width of about 0.90 μm, the filling at block **420** might reduce the depth of the gap to about 3.3 μm, a reduction in the height of about 40%.

[**0037**] Suitable values for the D/S ratio to fill the remainder of the gap at block **428** are values less than 10, as indicated at block **424**. These values are again determined by the processing parameters and provide an increased sputtering component to keep the gap open during deposition of the remainder of the film. After the gap has been filled, the plasma is extinguished at block **432** and the substrate is transferred out of the process chamber at block **436**.

[**0038**] The process has thus been described as an in situ process taking place in a single chamber with a continuous plasma, but these are not requirements of the invention. In alternative embodiments, the plasma may be extinguished and reinitiated for different parts of the process and the different parts of the process may be performed in different chambers.

[**0039**] Another embodiment of the invention is illustrated with the flow diagram of **FIG. 5** and makes use of an unexpected discovery by the inventors that a hydrogen plasma may be used to remove deposited silicon oxide. The removal proceeds chemically according to the reaction $SiO_2+2H_2 \rightarrow SiH_4+O_2$ and provides a relatively slow removal rate of about 50-100 Å/min, even with a H_2 flow rate to the chamber on the order of 1000 sccm. This slow removal rate provides an improved degree of precision over the removal process that is not available with alternative removal processes, such as chemical etching processes based on halogen chemistry or mechanical processes that provide processing conditions with a low D/S ratio to sputter material aggressively. The use of halogen-based etch chemistries, such as result from plasmas formed from flows of NF_3, may cause undesirable stress on the chamber ceramics because of the formation of aluminum halogen byproducts such as AlF_3.

[**0040**] In describing these embodiments, reference is made simultaneously to the flow diagram of **FIG. 5** and to **FIG. 6**, which provides simplified cross-sectional views of a structure at different points during the process described in connection with **FIG. 5**. The structure is shown as a substrate having trenches etched therein as part of an STI structure, but the principles described herein may be applied more generally to any structure that defines gaps to be filled, including IMD and PMD applications, among others. As shown in **FIG. 5**, the process starts by positioning a substrate in a process chamber at block **504**. The substrate has an initial structure **604** shown schematically in **FIG. 6** with features **620** that form one or more gaps to be filled. The features **620** may be, for example, areas of a substrate between etched trenches, adjacent metal lines, transistor gates, or other features. In some instances, the structure **604** may additionally include silicon nitride portions above the raised features and/or a silicon nitride liner along the interior of the gaps. The presence of such a line may increase the aspect ratio of the gap even further.

[**0041**] Once the substrate is properly positioned, flows of a silicon-containing gas like SiH_4, an oxygen-containing gas like O_2, and molecular hydrogen H_2 are provided to the chamber at block **508**. A high-density plasma is formed from the gas flows by inductively coupling rf energy into the chamber at block **512**, permitting the gap to be partially filled at block **516**. As explained above, the deposition at block **516** results in the formation of a cusp **636**, as shown for intermediate structure **608**, with redeposition causing silicate glass to be deposited more thickly near the corners of the underlying structures than on the sidewalls.

[**0042**] To remove some of the deposited silicate glass and reshape the gap for further deposition, the flows of the precursor silicon-containing and oxygen-containing gases, as well as flows of any dopant gases that may have been supplied, are terminated at block **520**. The removal of material results from the chemical interaction of the remaining hydrogen plasma to produce a further intermediate structure **612** that has a reduced cusp height **640** and a reshaped profile. While the principal removal mechanism results from the chemical interaction described above, it may be enhanced in certain embodiments. For instance, a bias may be applied to the substrate to attract the plasma ions and thereby introduce an anisotropy in the removal. Other anisotropies may be introduced by using different flows of the H_2 gas into the chamber to provide different flow characteristics throughout the chamber, allowing the removal to be performed selectively across the substrate as a whole. In addition, the plasma may comprise species other than hydrogen to increase the mechanical sputtering effect, although some embodiments of the invention generally remain limited to instances in which the average molecular weight of the sources is less than 5 amu.

[**0043**] Removal of material results in structure **612** by shaping the deposited film **640** so that the basic shape of the original features is retained, but with a less severe aspect ratio. After material has been removed to reopen the gap, flows of the precursor gases are reinitiated at block **528** so that the remainder of the gap may be filled at block **532** to produce structure **616** with film **644** providing substantially void-free gapfill. In many instances, the gap may be filled with two such deposition stages and a single intermediate removal stage, although more aggressive gaps may be filled with a greater number of interleaved deposition and removal stages. After the gap has been filled, the substrate is transferred out of the chamber at block **536**.

[**0044**] Again, the process has been described as an in situ process in which the deposition and removal stages are performed in a single chamber with a continuous plasma. In other embodiments, the plasma may be extinguished between stages, with gas flows and other parameters being adjusted in preparation for the next phase, and a plasma being reformed. Such embodiments may also be performed

as in situ processes in a single chamber (or in different chambers of a multichamber system), or may be performed as ex situ processes in different chambers. In some instances, in situ processes are preferred for throughput and performance reasons.

[0045] In other embodiments, the processes described in connection with **FIG. 4** regarding the use of a decreasing D/S ratio and the processes described in connection with **FIG. 5** regarding the chemical removal of silicate-glass material with a hydrogen-based plasma may be combined. **FIGS. 7A-7C** each provide flow diagrams that illustrate how the processes may be combined in different ways.

[0046] First, the change in D/S ratio used in **FIG. 4** may be integrated with the process of **FIG. 5** by having either or both of the depositions **516** and/or **532** use change in D/S ratio. Thus, **FIG. 7A** illustrates explicitly that block **516** of **FIG. 5** may comprise a first block **762** at which a first portion of the gap is filled with process conditions that provide a D/S ratio between 20 and 100 and a second block **764** at which a second portion of the gap is thereafter filled with process conditions that provide a D/S ratio less than 10. The inclusion of such an initially high D/S ratio is useful in avoiding corner clipping in open areas for the same reasons that were described above.

[0047] **FIG. 7B** similarly illustrates explicitly that block **532** of **FIG. 5** may comprise a first block **766** at which a first portion of the gap is filled with process conditions that provide a D/S ratio between 20 and 100 and a second block **768** at which a second portion of the gap is thereafter filled with process conditions that provide a D/S ratio less than 10. The inclusion of such a high D/S ratio after the removal of material at block **524** of **FIG. 5** may be useful under circumstances where the amount of material removed poses a risk of corner clipping in open areas because of the presence of insufficient material to protect the corners.

[0048] **FIG. 7C** illustrates a process in which the high D/S ratio is used initially, thereby providing protection against corner clipping in open areas, but uses the lower D/S ratio after the removal of material by exposure to a hydrogen plasma. Such an embodiment is suitable in applications where the removal of material is not so aggressive as to present a risk of corner clipping, even in open areas, there being sufficient silicate glass material remaining even after the removal to protect the corners. To perform such a process as an in situ process with a continuous plasma, the substrate is transferred into the chamber at block **704** and flows of a silicon-containing gas, an oxygen-containing gas, and H_2 are provided at block **708** so that a high-density plasma may be formed in the chamber at block **712**. The gap is partially filled at block **716** using process parameters that provide a D/S ratio between 20 and 100. Flows of the precursor silicon-containing and oxygen-containing gases are terminated at block **720** so that part of the deposited film may be removed with a hydrogen plasma at block **724**. The flows of the precursor silicon-containing and oxygen-containing gases are reinitiated at block **728**, and the process parameters are established so that the remainder of the gap is filled at block **732** with a D/S ratio less than 10. After completing the gap fill process, the substrate is transferred out of the chamber at block **736**.

Exemplary Substrate Processing System

[0049] The inventors have implemented embodiments of the invention with the ULTIMA™ system manufactured by APPLIED MATERIALS, INC., of Santa Clara, Calif., a general description of which is provided in commonly assigned U.S. Pat. No. 6,170,428, "SYMMETRIC TUNABLE INDUCTIVELY COUPLED HDP-CVD REACTOR," filed Jul. 15, 1996 by Fred C. Redeker, Farhad Moghadam, Hirogi Hanawa, Tetsuya Ishikawa, Dan Maydan, Shijian Li, Brian Lue, Robert Steger, Yaxin Wang, Manus Wong and Ashok Sinha, the entire disclosure of which is incorporated herein by reference. An overview of the system is provided in connection with **FIGS. 8A and 8B** below. **FIG. 8A** schematically illustrates the structure of such an HDP-CVD system **810** in one embodiment. The system **810** includes a chamber **813**, a vacuum system **870**, a source plasma system **880**A, a bias plasma system **880**B, a gas delivery system **833**, and a remote plasma cleaning system **850**.

[0050] The upper portion of chamber **813** includes a dome **814**, which is made of a ceramic dielectric material, such as aluminum oxide or aluminum nitride. Dome **814** defines an upper boundary of a plasma processing region **816**. Plasma processing region **816** is bounded on the bottom by the upper surface of a substrate **817** and a substrate support member **818**.

[0051] A heater plate **823** and a cold plate **824** surmount, and are thermally coupled to, dome **814**. Heater plate **823** and cold plate **824** allow control of the dome temperature to within about ±10° C. over a range of about 100° C. to 200° C. This allows optimizing the dome temperature for the various processes. For example, it may be desirable to maintain the dome at a higher temperature for cleaning or etching processes than for deposition processes. Accurate control of the dome temperature also reduces the flake or particle counts in the chamber and improves adhesion between the deposited layer and the substrate.

[0052] The lower portion of chamber **813** includes a body member **822**, which joins the chamber to the vacuum system. A base portion **821** of substrate support member **818** is mounted on, and forms a continuous inner surface with, body member **822**. Substrates are transferred into and out of chamber **813** by a robot blade (not shown) through an insertion/removal opening (not shown) in the side of chamber **813**. Lift pins (not shown) are raised and then lowered under the control of a motor (also not shown) to move the substrate from the robot blade at an upper loading position **857** to a lower processing position **856** in which the substrate is placed on a substrate receiving portion **819** of substrate support member **818**. Substrate receiving portion **819** includes an electrostatic chuck **820** that secures the substrate to substrate support member **818** during substrate processing. In a preferred embodiment, substrate support member **818** is made from an aluminum oxide or aluminum ceramic material.

[0053] Vacuum system **870** includes throttle body **825**, which houses twin-blade throttle valve **826** and is attached to gate valve **827** and turbo-molecular pump **828**. It should be noted that throttle body **825** offers minimum obstruction to gas flow, and allows symmetric pumping. Gate valve **827** can isolate pump **828** from throttle body **825**, and can also control chamber pressure by restricting the exhaust flow capacity when throttle valve **826** is fully open. The arrangement of the throttle valve, gate valve, and turbo-molecular pump allow accurate and stable control of chamber pressures up to about 1 millitorr to about 2 torr.

[0054] The source plasma system **880**A includes a top coil **829** and side coil **830**, mounted on dome **814**. A symmetrical ground shield (not shown) reduces electrical coupling between the coils. Top coil **829** is powered by top source RF (SRF) generator **831**A, whereas side coil **830** is powered by side SRF generator **831**B, allowing independent power levels and frequencies of operation for each coil. This dual coil system allows control of the radial ion density in chamber **813**, thereby improving plasma uniformity. Side coil **830** and top coil **829** are typically inductively driven, which does not require a complimentary electrode. In a specific embodiment, the top source RF generator **831**A provides up to 2,500 watts of RF power at nominally 2 MHz and the side source RF generator **831**B provides up to 5,000 watts of RF power at nominally 2 MHz. The operating frequencies of the top and side RF generators may be offset from the nominal operating frequency (e.g. to 1.7-1.9 MHz and 1.9-2.1 MHz, respectively) to improve plasma-generation efficiency.

[0055] A bias plasma system **880**B includes a bias RF ("BRF") generator **831**C and a bias matching network **832**C. The bias plasma system **880**B capacitively couples substrate portion **817** to body member **822**, which act as complimentary electrodes. The bias plasma system **880**B serves to enhance the transport of plasma species (e.g., ions) created by the source plasma system **880**A to the surface of the substrate. In a specific embodiment, bias RF generator provides up to 10,000 watts of RF power at a frequency less than 5 MHz, as discussed further below.

[0056] RF generators **831**A and **831**B include digitally controlled synthesizers and operate over a frequency range between about 1.8 to about 2.1 MHz. Each generator includes an RF control circuit (not shown) that measures reflected power from the chamber and coil back to the generator and adjusts the frequency of operation to obtain the lowest reflected power, as understood by a person of ordinary skill in the art. RF generators are typically designed to operate into a load with a characteristic impedance of 50 ohms. RF power may be reflected from loads that have a different characteristic impedance than the generator. This can reduce power transferred to the load. Additionally, power reflected from the load back to the generator may overload and damage the generator. Because the impedance of a plasma may range from less than 5 ohms to over 900 ohms, depending on the plasma ion density, among other factors, and because reflected power may be a function of frequency, adjusting the generator frequency according to the reflected power increases the power transferred from the RF generator to the plasma and protects the generator. Another way to reduce reflected power and improve efficiency is with a matching network.

[0057] Matching networks **832**A and **832**B match the output impedance of generators **831**A and **831**B with their respective coils **829** and **830**. The RF control circuit may tune both matching networks by changing the value of capacitors within the matching networks to match the generator to the load as the load changes. The RF control circuit may tune a matching network when the power reflected from the load back to the generator exceeds a certain limit. One way to provide a constant match, and effectively disable the RF control circuit from tuning the matching network, is to set the reflected power limit above any expected value of reflected power. This may help stabilize a plasma under some conditions by holding the matching network constant at its most recent condition.

[0058] Other measures may also help stabilize a plasma. For example, the RF control circuit can be used to determine the power delivered to the load (plasma) and may increase or decrease the generator output power to keep the delivered power substantially constant during deposition of a layer.

[0059] A gas delivery system **833** provides gases from several sources, **834**A-**834**E chamber for processing the substrate via gas delivery lines **838** (only some of which are shown). As would be understood by a person of skill in the art, the actual sources used for sources **834**A-**834**E and the actual connection of delivery lines **838** to chamber **813** varies depending on the deposition and cleaning processes executed within chamber **813**. Gases are introduced into chamber **813** through a gas ring **837** and/or a top nozzle **845**. **FIG. 8B** is a simplified, partial cross-sectional view of chamber **813** showing additional details of gas ring **837**.

[0060] In one embodiment, first and second gas sources, **834**A and **834**B, and first and second gas flow controllers, **835**A' and **835**B', provide gas to ring plenum **836** in gas ring **837** via gas delivery lines **838** (only some of which are shown). Gas ring **837** has a plurality of source gas nozzles **839** (only one of which is shown for purposes of illustration) that provide a uniform flow of gas over the substrate. Nozzle length and nozzle angle may be changed to allow tailoring of the uniformity profile and gas utilization efficiency for a particular process within an individual chamber. In a preferred embodiment, gas ring **837** has 12 source gas nozzles made from an aluminum oxide ceramic.

[0061] Gas ring **837** also has a plurality of oxidizer gas nozzles **840** (only one of which is shown), which in a preferred embodiment are co-planar with and shorter than source gas nozzles **839**, and in one embodiment receive gas from body plenum **841**. In some embodiments it is desirable not to mix source gases and oxidizer gases before injecting the gases into chamber **813**. In other embodiments, oxidizer gas and source gas may be mixed prior to injecting the gases into chamber **813** by providing apertures (not shown) between body plenum **841** and gas ring plenum **836**. In one embodiment, third, fourth, and fifth gas sources, **834**C, **834**D, and **834**D', and third and fourth gas flow controllers, **835**C and **835**D', provide gas to body plenum via gas delivery lines **838**. Additional valves, such as **843**B (other valves not shown), may shut off gas from the flow controllers to the chamber. In implementing certain embodiments of the invention, source **834**A comprises a silane SiH_4 source, source **834**B comprises a molecular oxygen O_2 source, source **834**C comprises a silane SiH_4 source, source **834**D comprises a helium He source, and source **834**D' comprises a molecular hydrogen H_2 source.

[0062] In embodiments where flammable, toxic, or corrosive gases are used, it may be desirable to eliminate gas remaining in the gas delivery lines after a deposition. This may be accomplished using a 3-way valve, such as valve **843**B, to isolate chamber **813** from delivery line **838**A and to vent delivery line **838**A to vacuum foreline **844**, for example. As shown in **FIG. 8A**, other similar valves, such as **843**A and **843**C, may be incorporated on other gas delivery lines. Such three-way valves may be placed as close to chamber **813** as practical, to minimize the volume of the

unvented gas delivery line (between the three-way valve and the chamber). Additionally, two-way (on-off) valves (not shown) may be placed between a mass flow controller ("MFC") and the chamber or between a gas source and an MFC.

[0063] Referring again to **FIG. 8A**, chamber **813** also has top nozzle **845** and top vent **846**. Top nozzle **845** and top vent **846** allow independent control of top and side flows of the gases, which improves film uniformity and allows fine adjustment of the film's deposition and doping parameters. Top vent **846** is an annular opening around top nozzle **845**. In one embodiment, first gas source **834**A supplies source gas nozzles **839** and top nozzle **845**. Source nozzle MFC **835**A' controls the amount of gas delivered to source gas nozzles **839** and top nozzle MFC **835**A controls the amount of gas delivered to top gas nozzle **845**. Similarly, two MFCs **835**B and **835**B' may be used to control the flow of oxygen to both top vent **846** and oxidizer gas nozzles **840** from a single source of oxygen, such as source **834**B. In some embodiments, oxygen is not supplied to the chamber from any side nozzles. The gases supplied to top nozzle **845** and top vent **846** may be kept separate prior to flowing the gases into chamber **813**, or the gases may be mixed in top plenum **848** before they flow into chamber **813**. Separate sources of the same gas may be used to supply various portions of the chamber.

[0064] A remote microwave-generated plasma cleaning system **850** is provided to periodically clean deposition residues from chamber components. The cleaning system includes a remote microwave generator **851** that creates a plasma from a cleaning gas source **834**E (e.g., molecular fluorine, nitrogen trifluoride, other fluorocarbons or equivalents) in reactor cavity **853**. The reactive species resulting from this plasma are conveyed to chamber **813** through cleaning gas feed port **854** via applicator tube **855**. The materials used to contain the cleaning plasma (e.g., cavity **853** and applicator tube **855**) must be resistant to attack by the plasma. The distance between reactor cavity **853** and feed port **854** should be kept as short as practical, since the concentration of desirable plasma species may decline with distance from reactor cavity **853**. Generating the cleaning plasma in a remote cavity allows the use of an efficient microwave generator and does not subject chamber components to the temperature, radiation, or bombardment of the glow discharge that may be present in a plasma formed in situ. Consequently, relatively sensitive components, such as electrostatic chuck **820**, do not need to be covered with a dummy wafer or otherwise protected, as may be required with an in situ plasma cleaning process. In **FIG. 8A**, the plasma-cleaning system **850** is shown disposed above the chamber **813**, although other positions may alternatively be used.

[0065] A baffle **861** may be provided proximate the top nozzle to direct flows of source gases supplied through the top nozzle into the chamber and to direct flows of remotely generated plasma. Source gases provided through top nozzle **845** are directed through a central passage **862** into the chamber, while remotely generated plasma species provided through the cleaning gas feed port **854** are directed to the sides of the chamber **813** by the baffle **861**.

[0066] Those of ordinary skill in the art will realize that specific parameters can vary for different processing chambers and different processing conditions, without departing from the spirit of the invention. Other variations will also be apparent to persons of skill in the art. These equivalents and alternatives are intended to be included within the scope of the present invention. Therefore, the scope of this invention should not be limited to the embodiments described, but should instead be defined by the following claims.

What is claimed is:

1. A method of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber, the substrate having a gap formed between adjacent raised surfaces, the method comprising:

flowing a silicon-containing gas into the substrate processing chamber;

flowing an oxygen-containing gas into the substrate processing chamber;

flowing a fluent gas having an average molecular weight less than 5 amu into the substrate processing chamber;

forming a first high-density plasma from the silicon-containing gas, the oxygen-containing gas, and the fluent gas to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a first deposition/sputter ratio; and

forming a second high-density plasma from the silicon-containing gas, the oxygen-containing gas, and the fluent gas to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a second deposition/sputter ratio, wherein the second deposition/sputter ratio is less than the first deposition/sputter ratio,

wherein each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

2. The method recited in claim 1 wherein the first deposition/sputter ratio is between 20 and 100.

3. The method recited in claim 2 wherein the second deposition/sputter ratio is less than 10.

4. The method recited in claim 1 wherein forming the second high-density plasma comprising changing process conditions without extinguishing the first high-density plasma.

5. The method recited in claim 1 wherein the fluent gas comprises molecular hydrogen H_2.

6. The method recited in claim 5 wherein the molecular hydrogen H_2 is flowed into the substrate processing chamber with a flow rate greater than 500 sccm.

7. The method recited in claim 1 wherein the fluent gas comprises helium He.

8. The method recited in claim 1 wherein the silicon-containing gas comprises monosilane SiH_4 and the oxygen-containing gas comprises molecular oxygen O_2.

9. The method recited in claim 1 wherein the first portion of the silicon oxide film reduces a depth of the gap by less than 50%.

10. The method recited in claim 1 wherein the gap comprises a plurality of gaps formed between adjacent

raised surfaces, a first of the gaps having a width at least five times a width of a second of the gaps.

11. A method of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber, the substrate having a plurality of gaps formed between adjacent raised surfaces, a first of the gaps having a width at least five times a width of a second of the gaps, the method comprising:

flowing monosilane SiH_4 into the substrate processing chamber;

flowing molecular oxygen O_2 into the substrate processing chamber;

flowing molecular hydrogen H_2 into the substrate processing chamber at a flow rate greater than 500 sccm;

forming a first high-density plasma from the monosilane SiH_4, the molecular oxygen O_2, and the molecular hydrogen H_2 to deposit a first portion of the silicon oxide film over the substrate and within each of the first and second gaps with a first deposition process that has simultaneous deposition and sputtering components having relative contributions defined by a first deposition/sputter ratio between 20 and 100; and

forming a second high-density plasma from the monosilane SiH_4, the molecular oxygen O_2, and the molecular hydrogen H_2 to deposit a second portion of the silicon oxide film over the substrate and within each of the first and second gaps with a second deposition process that has simultaneous deposition and sputtering having relative contributions defined by a second deposition/sputter ratio less than 10,

wherein each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

12. A method of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber, the substrate having a gap formed between adjacent raised surfaces, the method comprising:

providing a flow of a first gaseous mixture to the substrate processing chamber, the flow of the first gaseous mixture comprising a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas;

forming a first high-density plasma from the first gaseous mixture to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components;

exposing the first portion of the silicon oxide film to a second high-density plasma formed with a flow of gases having an average molecular weight less than 5 amu and including a flow of molecular hydrogen H_2;

thereafter, providing a flow of a second gaseous mixture to the substrate processing chamber, the flow of the second gaseous mixture comprising a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas; and

forming a third high-density plasma from the second gaseous mixture to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components.

13. The method recited in claim 12 wherein the second high-density plasma is formed with a flow that consists essentially of molecular hydrogen H_2.

14. The method recited in claim 12 wherein exposing the first portion to the second high-density plasma comprises terminating the flow of the silicon-containing gas and the flow of the oxygen-containing gas comprised by the flow of the first gaseous mixture.

15. The method recited in claim 14 wherein providing the flow of the second gaseous mixture comprises reinitiating the terminated flow of the silicon-containing gas and the terminated flow of the oxygen-containing gas.

16. The method recited in claim 12 wherein the flow of molecular hydrogen H_2 is provided at a rate greater than 500 sccm.

17. The method recited in claim 12 wherein the flow of molecular hydrogen H_2 is provided at a rate greater than 1000 sccm.

18. The method recited in claim 12 further comprising:

exposing the second portion of the silicon oxide film to a fourth high-density plasma formed with a flow of gases having an average molecular weight less than 5 amu and including a flow of molecular hydrogen H_2;

thereafter, providing a flow of a third gaseous mixture to the substrate processing chamber, the flow of the third gaseous mixture comprising a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas; and

forming a fifth high-density plasma from the third gaseous mixture to deposit a third portion of the silicon oxide film over the substrate and within the gap with a third deposition process that has simultaneous deposition and sputtering components.

19. The method recited in claim 12 wherein:

the first deposition process comprises relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100;

the second deposition process comprises relative deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10; and

each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

20. The method recited in claim 12 wherein the first deposition process comprises:

a first part having relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100; and

a second part having relative deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10,

wherein the second part temporally follows the first part and each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

21. The method recited in claim 12 wherein the second deposition process comprises:

a first part having relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100; and

a second part having relative deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10,

wherein the second part temporally follows the first part and each of the first and second deposition/sputter ratios is defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

22. A method of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber, the substrate having a gap formed between adjacent raised surfaces, the method comprising:

providing a flow of a first gaseous mixture to the substrate processing chamber, the flow of the first gaseous mixture comprising a flow of monosilane SiH_4, a flow of molecular oxygen O_2, and a flow of molecular hydrogen H_2 at a flow rate greater than 500 sccm;

forming a first high-density plasma from the first gaseous mixture to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components;

terminating the flow of the monosilane SiH_4 and the flow of the molecular oxygen O_2 to expose the first portion of the silicon oxide film to a second high-density plasma formed from the flow of the molecular hydrogen H_2, wherein the flow rate of the molecular hydrogen H_2 is maintained greater than 500 sccm;

reinitiating the terminated flow of the monosilane SiH_4 and the terminated flow of the molecular oxygen O_2 to form a third high-density plasma to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components.

23. The method recited in claim 22 wherein:

the gap comprises a plurality of gaps formed between adjacent raised surfaces, a first of the gaps having a width at least five times a width of a second of the gaps;

the first deposition process comprises relative deposition and sputtering contributions defined by a first deposition/sputter ratio between 20 and 100; and

the second deposition process comprises relative deposition and sputtering contributions defined by a second deposition/sputter ratio less than 10,

each of the first and second deposition/sputter ratios being defined as a ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate.

24. A method of depositing a silicon oxide film on a substrate disposed in a substrate processing chamber, the substrate having a gap formed between adjacent raised surfaces, the method comprising:

providing a flow of a first gaseous mixture to the substrate processing chamber, the flow of the first gaseous mixture comprising a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas;

forming a first high-density plasma from the first gaseous mixture to deposit a first portion of the silicon oxide film over the substrate and within the gap with a first deposition process that has simultaneous deposition and sputtering components;

exposing the first portion of the silicon oxide film to a second high-density plasma formed with a flow of gases that includes a flow of molecular hydrogen H_2 and does not include a halogen;

thereafter, providing a flow of a second gaseous mixture to the substrate processing chamber, the flow of the second gaseous mixture comprising a flow of a silicon-containing gas, a flow of an oxygen-containing gas, and a flow of a fluent gas; and

forming a third high-density plasma from the second gaseous mixture to deposit a second portion of the silicon oxide film over the substrate and within the gap with a second deposition process that has simultaneous deposition and sputtering components.

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